FUJITSU SEMICONDUCTOR
DATA SHEET

DS05-11416-1E

MEMORY Mobile FCRAM™

CMOS

16 Mbit (1 M word × 16 bit)
Mobile Phone Application Specific Memory

MB82D01171B-60L/-60LL/-70L/-70LL

CMOS 1,048,576-WORD × 16 BIT
Fast Cycle Random Access Memory
with Low Power SRAM Interface

■ DESCRIPTION

The Fujitsu MB82D01171B is a CMOS Fast Cycle Random Access Memory (FCRAM) with asynchronous Static Random Access Memory (SRAM) interface containing 16,777,216 storages accessible in a 16-bit format. This MB82D01171B is suited for mobile applications such as Cellular Handset and PDA.

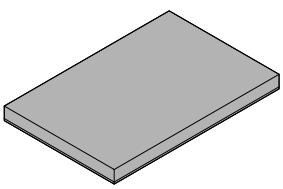
Note: FCRAM is a trademark of Fujitsu Limited, Japan.

■ PRODUCT LINEUP

Parameter	MB82D01171B			
	60L	60LL	70L	70LL
Access Time (t_{AA} Max, t_{CE} Max)	60 ns		70 ns	
Active Current (I_{DDA1} Max)	20 mA			
Standby Current (I_{DDS1} Max)	100 µA	70 µA	100 µA	70 µA
Power Down Current (I_{DDP} Max)	10 µA			

■ PACKAGES

48-ball plastic FBGA



(BGA-48P-M18)

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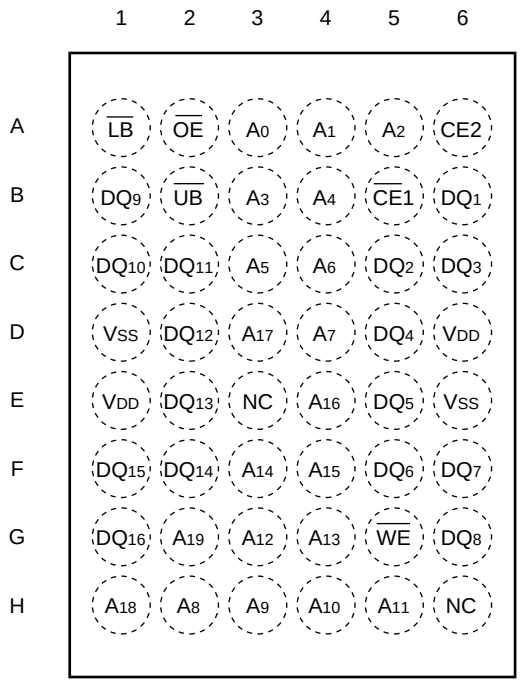
■ FEATURES

- Asynchronous SRAM Interface
- 1 M word × 16 bit Organization
- Fast Random Access Time : $t_{AA} = t_{CE} = 60$ ns, 70 ns
- Low Power Consumption : $I_{DDS1} = 100$ µA (L version) , 70 µA (LL version)
- Wide Operating Conditions : $V_{DD} = +2.3$ V to +2.7 V
  +2.7 V to +3.1 V
  +3.1 V to +3.5 V
  $T_A = -30$ °C to +85 °C
- Byte Write Control
- 8 words Address Access Capability
- Power Down Control by CE2

■ PIN ASSIGNMENTS

(TOP VIEW)

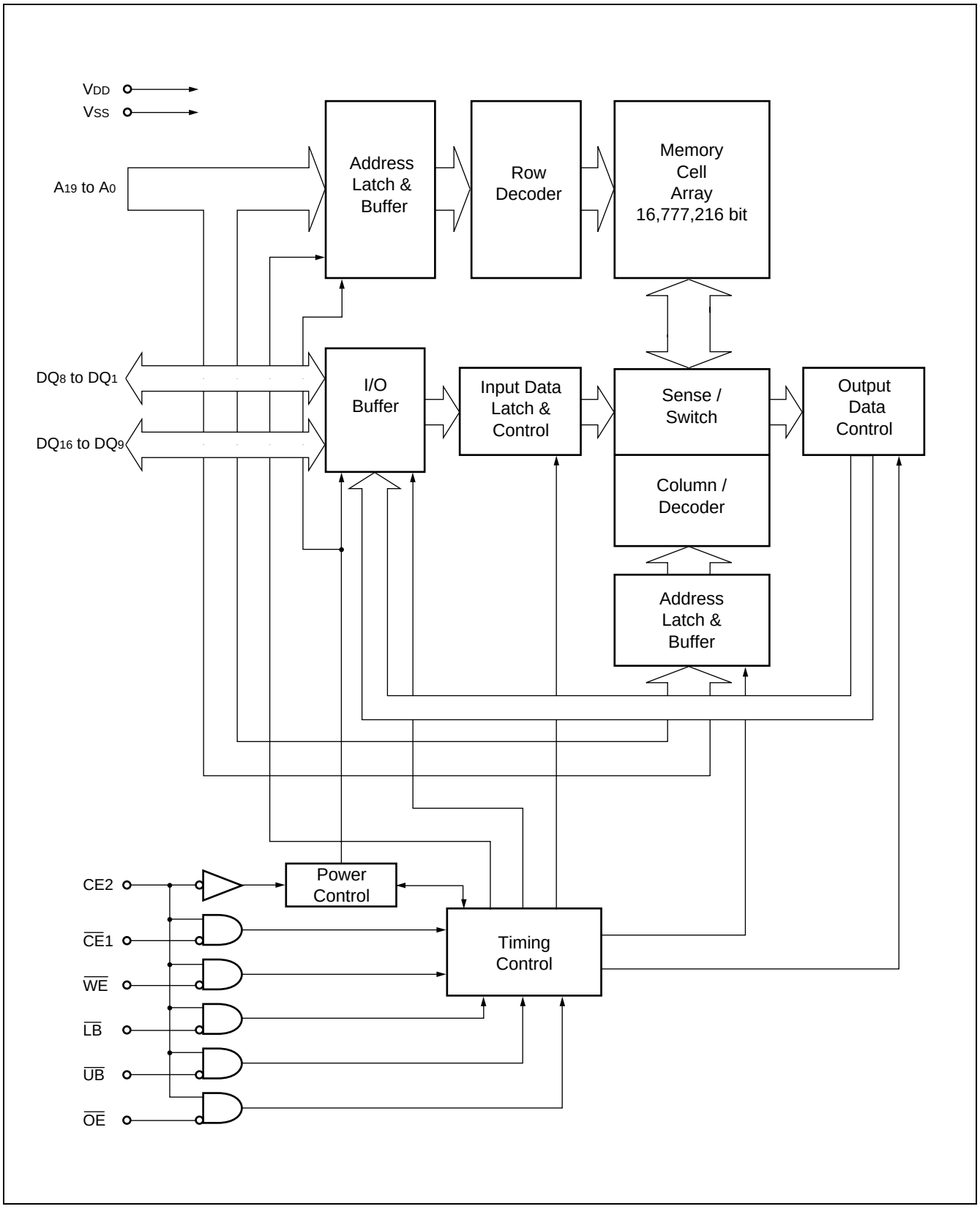


(BGA-48P-M18)

■ PIN DESCRIPTION

Pin Name	Description
A_{19} to A_0	Address Input
$\overline{CE}1$	Chip Enable (Low Active)
CE2	Chip Enable (High Active)
$\overline{WE}$	Write Enable (Low Active)
$\overline{OE}$	Output Enable (Low Active)
$\overline{LB}$	Lower Byte Write Control (Low Active)
$\overline{UB}$	Upper Byte Write Control (Low Active)
DQ_8 to DQ_1	Lower Byte Data Input/Output
DQ_{16} to DQ_9	Upper Byte Data Input/Output
V_{DD}	Power Supply
V_{SS}	Ground
NC	No Connection

■ BLOCK DIAGRAM



■ FUNCTION TRUTH TABLE

Mode	CE2	$\overline{CE}$1	$\overline{WE}$	$\overline{OE}$	$\overline{LB}$	$\overline{UB}$	A_{19} to A_0	DQ_8 to DQ_1	DQ_{16} to DQ_9	I_{DD}	Data Retention
Standby (Deselect)	H	H	X	X	X	X	X	High-Z	High-Z	I_{DDS}	Yes
Output Disable*1	L	H	H	X	X	*5	High-Z	High-Z	I_{DDA}	
No Read		H	L	H	H	Valid	High-Z	High-Z		
Read*2				L *4	L *4	Valid	Output Valid	Output Valid		
Write (Upper Byte)		L	H	L	H	L	Valid	Invalid	Input Valid		
Write (Lower Byte)			L	H	L	H	Valid	Input Valid	Invalid		
Write (Word)					L	L	Valid	Input Valid	Input Valid		
Power Down *3	L	X	X	X	X	X	X	High-Z	High-Z	I_{DDP}	No

Note : L = Logic Low, H = Logic High, X = either “L” or “H”, High-Z = High Impedance

*1 : Output Disable mode should not be kept longer than 1 μs.

*2 : Byte control at Read mode is not supported.

*3 : Power Down mode can be entered from Standby state and all DQ pins are in High-Z state.

*4 : Either or both $\overline{LB}$ and $\overline{UB}$ must be Low for Read operation.

*5 : Can be either V_{IL} or V_{IH} but must be valid before Read or Write.

■ ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Rating		Unit
		Min	Max	
Voltage of V_{DD} Supply Relative to V_{SS}	V_{DD}	–0.5	+3.6	V
Voltage at Any Pin Relative to V_{SS}	V_{IN}	–0.5	+3.6	V
	V_{OUT}	–0.5	+3.6	V
Short Circuit Output Current	I_{OUT}	–50	+50	mA
Storage Temperature	T_{STG}	–55	+125	°C

WARNING: Semiconductor devices can be permanently damaged by application of stress (voltage, current, temperature, etc.) in excess of absolute maximum ratings. Do not exceed these ratings.

■ RECOMMENDED OPERATING CONDITIONS

Parameter	Symbol	Value		Unit
		Min	Max	
Supply Voltage *1	V_{DD} (31)	3.1	3.5	V
	V_{DD} (27)	2.7	3.1	V
	V_{DD} (23)	2.3	2.7	V
	V_{SS}	0	0	V
High Level Input Voltage *1, *2	V_{IH} (31)	2.6	V_{DD} + 0.3 and ≤ 3.6	V
	V_{IH} (27)	2.2	V_{DD} + 0.3	V
	V_{IH} (23)	2.0	V_{DD} + 0.3	V
Low Level Input Voltage *1, *3	V_{IL} (31)	–0.3	0.6	V
	V_{IL} (27)	–0.3	0.5	V
	V_{IL} (23)	–0.3	0.4	V
Ambient Temperature	T_A	–30	85	°C

*1 : All voltages are referenced to V_{SS}.

*2 : Maximum DC voltage on input and I/O pins are V_{DD} + 0.3 V. During voltage transitions, inputs may overshoot to V_{DD} + 1.0 V for periods of up to 5 ns.

*3 : Minimum DC voltage on input or I/O pins are –0.3 V. During voltage transitions, inputs may undershoot V_{SS} to –1.0 V for periods of up to 5 ns.

WARNING: The recommended operating conditions are required in order to ensure the normal operation of the semiconductor device. All of the device's electrical characteristics are warranted when the device is operated within these ranges.

Always use semiconductor devices within their recommended operating condition ranges. Operation outside these ranges may adversely affect reliability and could result in device failure.

No warranty is made with respect to uses, operating conditions, or combinations not represented on the data sheet. Users considering application outside the listed conditions are advised to contact their FUJITSU representatives beforehand.

■ PIN CAPACITANCE

(f = 1.0 MHz, T_A = +25 °C)

Parameter	Symbol	Conditions	Value			Unit
			Min	Typ	Max	
Address Input Capacitance	C_{IN1}	V_{IN} = 0 V	—	—	5	pF
Control Input Capacitance	C_{IN2}	V_{IN} = 0 V	—	—	5	pF
Data Input/Output Capacitance	C_{IO}	V_{IO} = 0 V	—	—	8	pF

■ DC CHARACTERISTICS

Parameter		Symbol	Conditions		Value		Unit
					Min	Max	
Input Leakage Current		I_{LI}	$V_{SS} \le V_{IN} \le V_{DD}$		–1.0	+1.0	µA
Output Leakage Current		I_{LO}	0 V ≤ $V_{OUT} \le V_{DD}$, Output Disable		–1.0	+1.0	µA
Output High Voltage Level		$V_{OH(31)}$	$V_{DD} = V_{DD(31)}$, I_{OH} = –0.5 mA		2.5	—	V
		$V_{OH(27)}$	$V_{DD} = V_{DD(27)}$, I_{OH} = –0.5 mA		2.2	—	V
		$V_{OH(23)}$	$V_{DD} = V_{DD(23)}$, I_{OH} = –0.5 mA		1.8	—	V
Output Low Voltage Level		V_{OL}	I_{OL} = 1 mA		—	0.4	V
V_{DD} Power Down Current		I_{DDP}	$V_{DD} = V_{DD}$ Max, $V_{IN} = V_{IH}$ or V_{IL}, CE2 ≤ 0.2 V		—	10	µA
V_{DD} Standby Current	L Version	I_{DDS}	$V_{DD} = V_{DD(31)}$ Max, $V_{IN} = V_{DD}$ – 0.5 V or V_{IL}, $\overline{CE}1$ = CE2 = V_{IH}		—	2.0	mA
	LL Version				—	1.5	
	L Version		$V_{DD} = V_{DD(27, 23)}$ Max, $V_{IN} = V_{DD}$ – 0.5 V or V_{IL}, $\overline{CE}1$ = CE2 = V_{IH}		—	1.0	mA
	LL Version				—	0.5	
	L Version	I_{DDS1}	$V_{DD} = V_{DD(31)}$ Max, $V_{IN} \le 0.2$ V or $V_{IN} \ge V_{DD}$ – 0.2 V, $\overline{CE}1$ = CE2 ≥ V_{DD} – 0.2 V		—	150	µA
	LL Version				—	100	
	L Version		$V_{DD} = V_{DD(27, 23)}$ Max, $V_{IN} \le 0.2$ V or $V_{IN} \ge V_{DD}$ – 0.2 V, $\overline{CE}1$ = CE2 ≥ V_{DD} – 0.2 V		—	100	µA
	LL Version				—	70	
V_{DD} Active Current		I_{DDA1}	$V_{DD} = V_{DD}$ Max, $V_{IN} = V_{DD}$ – 0.5 V or V_{IL}, $\overline{CE}1 = V_{IL}$ and CE2 = V_{IH}, I_{OUT} = 0 mA	t_{RC} / t_{WC} = Min	—	20	mA
		I_{DDA2}	$V_{DD} = V_{DD}$ Max, $V_{IN} = V_{DD}$ – 0.5 V or V_{IL}, $\overline{CE}1 = V_{IL}$ and CE2 = V_{IH}, I_{OUT} = 0 mA	t_{RC} / t_{WC} = 1 µs	—	3.0	mA

Notes: • All voltages are referenced to Vss.
• DC Characteristics are measured after following POWER-UP timing.
• I_{OUT} depends on the output load conditions.

■ AC CHARACTERISTICS

(1) Read Operation

Parameter	Symbol	-60L/-60LL		-70L/-70LL		Unit	Notes
		Min	Max	Min	Max		
Read Cycle Time	t_{RC}	80	—	90	—	ns	
Chip Enable Access Time	t_{CE}	—	60	—	70	ns	*1, *3
Output Enable Access Time	t_{OE}	—	35	—	40	ns	*1
Address Access Time	t_{AA}	—	60	—	70	ns	*1, *4
Output Data Hold Time	t_{OH}	5	—	5	—	ns	*1
$\overline{CE}$1 Low to Output Low-Z	t_{CLZ}	5	—	5	—	ns	*2
$\overline{OE}$ Low to Output Low-Z	t_{OLZ}	0	—	0	—	ns	*2
$\overline{CE}$1 High to Output High-Z	t_{CHZ}	—	20	—	25	ns	*2
$\overline{OE}$ High to Output High-Z	t_{OHZ}	—	20	—	25	ns	*2
Address Setup Time to $\overline{CE}$1 Low	t_{ASC}	–5	—	–5	—	ns	*5
Address Setup Time to $\overline{OE}$ Low	t_{ASO}	25	—	30	—	ns	*3, *6
	$t_{ASO[ABS]}$	5	—	5	—	ns	*7
$\overline{LB}$/$\overline{UB}$ Setup Time to $\overline{CE}$1 Low	t_{BSC}	–5	—	–5	—	ns	*5
$\overline{LB}$/$\overline{UB}$ Setup Time to $\overline{OE}$ Low	t_{BSO}	0	—	0	—	ns	
Address Invalid Time	t_{AX}	—	5	—	5	ns	*4, *8
Address Hold Time from $\overline{CE}$1Low	t_{CLAH}	80	—	90	—	ns	*4
Address Hold Time from $\overline{OE}$ Low	t_{OLAH}	45	—	50	—	ns	*4, *9
Address Hold Time from $\overline{CE}$1 High	t_{CHAH}	–5	—	–5	—	ns	
Address Hold Time from $\overline{OE}$ High	t_{OHAH}	–5	—	–5	—	ns	
$\overline{LB}$/$\overline{UB}$ Hold Time from $\overline{CE}$1 High	t_{CHBH}	–5	—	–5	—	ns	
$\overline{LB}$/$\overline{UB}$ Hold Time from $\overline{OE}$ High	t_{OHBH}	–5	—	–5	—	ns	
$\overline{CE}$1 Low to $\overline{OE}$ Low Delay Time	t_{CLOL}	25	1000	30	1000	ns	*3, *6, *9, *10
$\overline{OE}$ Low to $\overline{CE}$1 High Delay Time	t_{OLCH}	45	—	50	—	ns	*9
$\overline{CE}$1 High Pulse Width	t_{CP}	10	—	12	—	ns	
$\overline{OE}$ High Pulse Width	t_{OP}	25	1000	30	1000	ns	*6, *9, *10
	$t_{OP[ABS]}$	10	—	10	—	ns	*7

*1 : The output load is 50 pF + 1TTL.

*2 : The output load is 5 pF.

*3 : The t_{CE} is applicable if $\overline{OE}$ is brought to Low before $\overline{CE}$1 goes Low and is also applicable if actual value of both or either t_{ASO} or t_{CLOL} is shorter than specified value.

*4 : Applicable only to A_2, A_1 and A_0 when both $\overline{CE}$1 and $\overline{OE}$ are kept at Low for the address access.

*5 : Applicable if $\overline{OE}$ is brought to Low before $\overline{CE}$1 goes Low.

*6 : The t_{ASO}, t_{CLOL} (Min) and t_{OP} (Min) are reference values when the access time is determined by t_{OE}.
If actual value of each parameter is shorter than specified minimum value, t_{OE} become longer by the amount of subtracting actual value from specified minimum value.
For example, if actual t_{ASO}, t_{ASO} (actual) , is shorter than specified minimum value, t_{ASO} (Min) , during $\overline{OE}$ control access (i.e., $\overline{CE}$1 stays Low) , the t_{OE} become t_{OE} (Max) + t_{ASO} (Min) – t_{ASO} (actual) .

*7 : The $t_{ASO[ABS]}$ and $t_{OP[ABS]}$ is the absolute minimum value during $\overline{OE}$ control access.

*8 : The t_{AX} is applicable when all or two addresses among A_2 to A_0 are switched from previous state.

*9 : If actual value of either t_{CLOL} or t_{OP} is shorter than specified minimum value, both t_{OLAH} and t_{OLCH} become t_{RC} (Min) – t_{CLOL} (actual) or t_{RC} (Min) – t_{OP} (actual) .

*10 : Maximum value is applicable if $\overline{CE}$1 is kept at Low.

(2) Write Operation

Parameter	Symbol	-60L/-60LL		-70L/-70LL		Unit	Notes
		Min	Max	Min	Max		
Write Cycle Time	t_{WC}	80	—	90	—	ns	*1
Address Setup Time	t_{AS}	0	—	0	—	ns	*2, *9
Address Hold Time	t_{AH}	35	—	40	—	ns	*2
$\overline{CE}1$ Write Setup Time	t_{CS}	0	1000	0	1000	ns	*9
$\overline{CE}1$ Write Hold Time	t_{CH}	0	1000	0	1000	ns	
$\overline{WE}$ Setup Time	t_{WS}	0	—	0	—	ns	
$\overline{WE}$ Hold Time	t_{WH}	0	—	0	—	ns	
$\overline{LB}$ and $\overline{UB}$ Setup Time	t_{BS}	–5	—	–5	—	ns	
$\overline{LB}$ and $\overline{UB}$ Hold Time	t_{BH}	–5	—	–5	—	ns	
$\overline{OE}$ Setup Time	t_{OES}	0	1000	0	1000	ns	*3
$\overline{OE}$ Hold Time	t_{OEH}	25	1000	35	1000	ns	*3, *4
	$t_{OEH[ABS]}$	12	—	15	—	ns	*5
$\overline{OE}$ High to $\overline{CE}1$ Low Setup Time	t_{OHCL}	–5	—	–5	—	ns	*6
Address Hold Time from $\overline{OE}$ High	t_{OHAH}	–5	—	–5	—	ns	*7
$\overline{CE}1$ Write Pulse Width	t_{CW}	45	—	50	—	ns	*1, *8
$\overline{WE}$ Write Pulse Width	t_{WP}	45	—	50	—	ns	*1, *8, *9
$\overline{CE}1$ Write Recovery Time	t_{WRC}	20	—	20	—	ns	*1, *10
$\overline{WE}$ Write Recovery Time	t_{WR}	20	1000	20	1000	ns	*1, *3, *10
Data Setup Time	t_{DS}	15	—	20	—	ns	
Data Hold Time	t_{DH}	0	—	0	—	ns	
$\overline{CE}1$ High Pulse Width	t_{CP}	10	—	12	—	ns	*10

*1 : Minimum value must be equal or greater than the sum of actual t_{CW} (or t_{WP}) and t_{WRC} (or t_{WR}) .

*2 : New write address is valid from either $\overline{CE}1$ or $\overline{WE}$ is brought to High.

*3 : Maximum value is applicable if $\overline{CE}1$ is kept at Low and both $\overline{WE}$ and $\overline{OE}$ are kept at High.

*4 : The t_{OEH} is specified from end of t_{WC} (Min). The t_{OEH} (Min) is a reference value when access time is determined by t_{OE}. If actual value is shorter than specified minimum value, t_{OE} become longer by the amount of subtracting actual value from specified minimum value.

*5 : The $t_{OEH[ABS]}$ is the absolute minimum value if write cycle is terminated by $\overline{WE}$ and $\overline{CE}1$ stays Low.

*6 : t_{OHCL} (Min) must be satisfied if read operation is not performed prior to write operation.
In case $\overline{OE}$ is disabled after t_{OHCL} (Min) , $\overline{WE}$ Low must be asserted after t_{RC} (Min) from $\overline{CE}1$ Low.
In other words, read operation is initiated if t_{OHCL} (Min) is not satisfied.

*7 : Applicable if $\overline{CE}1$ stays Low after read operation.

*8 : t_{CW} and t_{WP} is applicable if write operation is initiated by $\overline{CE}1$ and $\overline{WE}$, respectively.

*9 : If write operation is terminated by $\overline{WE}$ followed by $\overline{CE}1$ = High, the sum of actual t_{CS} and t_{WP}, and the sum of actual t_{AS} and t_{WP} must be equal or greater than 60 ns. For example, if actual t_{WP} is 45 ns, t_{CS} and t_{AS} must be equal or greater than 15 ns.

*10 : t_{WRC} and t_{WR} is applicable if write operation is terminated by $\overline{CE}1$ and $\overline{WE}$, respectively.
In case $\overline{CE}1$ is brought to High before satisfaction of t_{WR} (Min) , the t_{WRC} (Min) is also applied.

(3) Power Down Parameters

Parameter	Symbol	-60L/-60LL		-70L/-70LL		Unit	Note
		Min	Max	Min	Max		
CE2 Low Setup Time for Power Down Entry	t_{CSP}	10	—	10	—	ns	
CE2 Low Hold Time after Power Down Entry	t_{C2LP}	80	—	90	—	ns	
$\overline{CE}$1 High Hold Time following CE2 High after Power Down Exit	t_{CHH}	350	—	350	—	µs	
$\overline{CE}$1 High Setup Time following CE2 High after Power Down Exit	t_{CHS}	10	—	10	—	ns	

(4) Other Timing Parameters

Parameter	Symbol	-60L/-60LL		-70L/-70LL		Unit	Note
		Min	Max	Min	Max		
$\overline{CE}$1 High to $\overline{OE}$ Invalid Time for Standby Entry	t_{CHOX}	10	—	10	—	ns	
$\overline{CE}$1 High to $\overline{WE}$ Invalid Time for Standby Entry	t_{CHWX}	10	—	10	—	ns	*1
CE2 Low Hold Time after Power-up	t_{C2LH}	50	—	50	—	µs	*2
CE2 High Hold Time after Power-up	t_{C2HL}	50	—	50	—	µs	*3
$\overline{CE}$1 High Hold Time following CE2 High after Power-up	t_{CHH}	350	—	350	—	µs	*2
$\overline{CE}$1 and CE2 High Hold Time during Power-up	t_{CHHP}	400	—	400	—	µs	
Input Transition Time	t_T	1	25	1	25	ns	*4

*1: It may write some data into any address location if t_{CHWX} (Min) is not satisfied.

*2: Must satisfy t_{CHH} (Min) after t_{C2LH} (Min) .

*3: Requires Power Down mode entry and exit after t_{C2HL}.

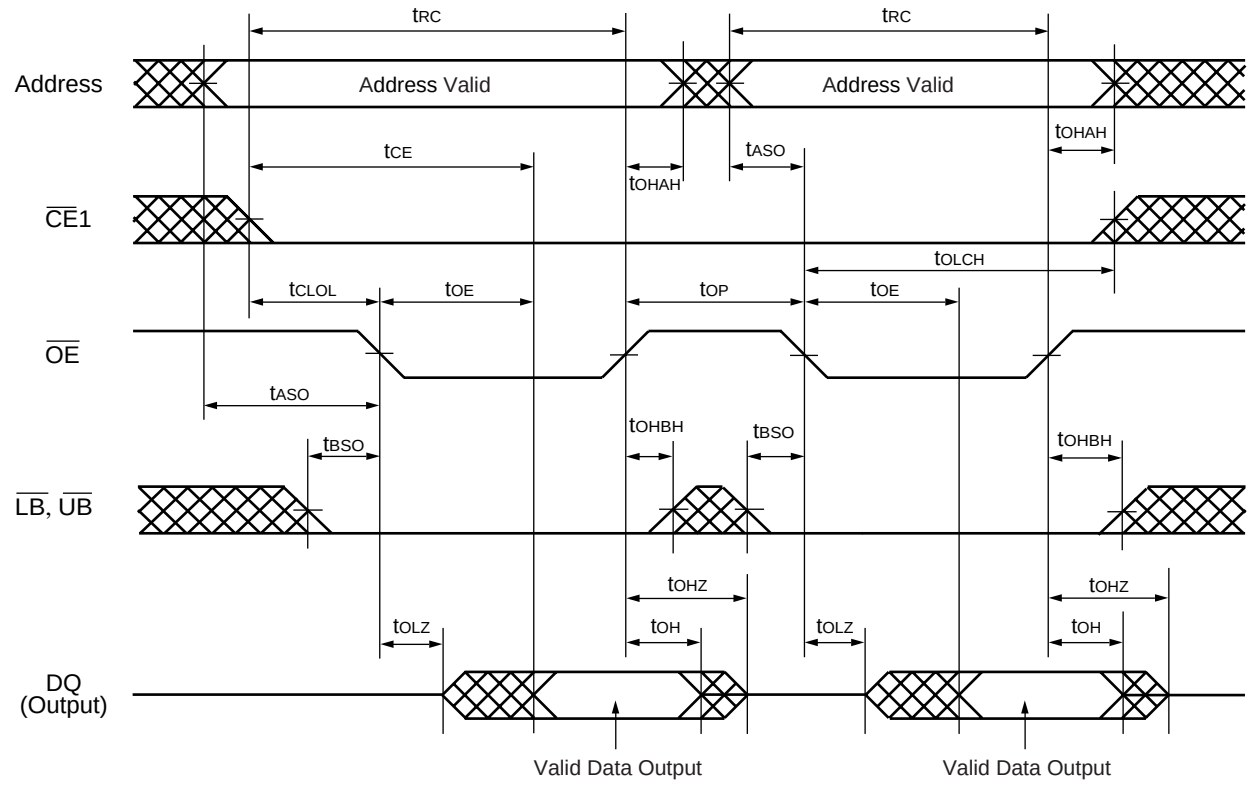
*4: The Input Transition Time (t_T) at AC testing is 5 ns as shown in below. If actual t_T is longer than 5 ns, each AC specification must be relaxed accordingly.

(5) AC Test Conditions

Parameter	Symbol	Conditions	Measured Value	Unit	Note
Input High Level	V_{IH}	—	V_{DD} – 0.4	V	
Input Low level	V_{IL}	—	0.4	V	
Input Timing Measurement Level	V_{REF}	—	1.3	V	
Input Transition Time	t_T	Between V_{IL} and V_{IH}	5	ns	

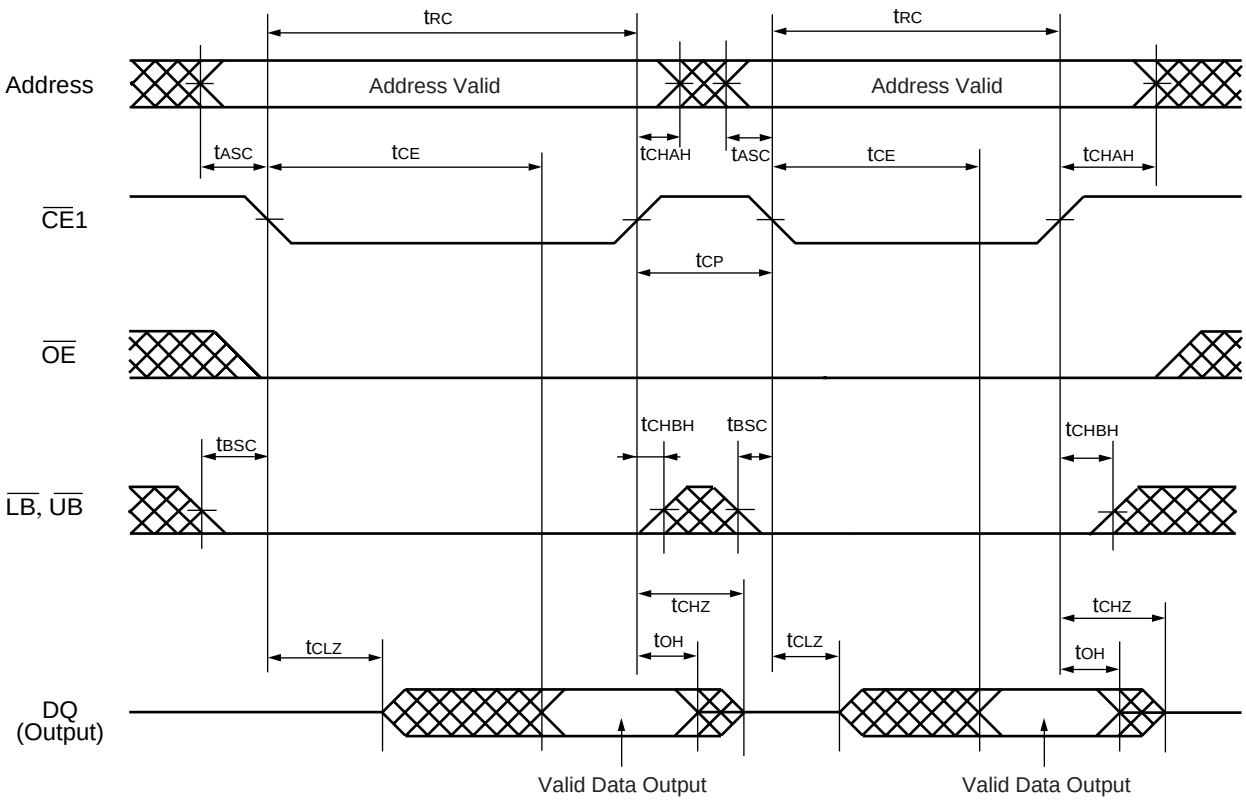
■ TIMING DIAGRAM

1. READ Timing #1 ($\overline{OE}$ Control Access)



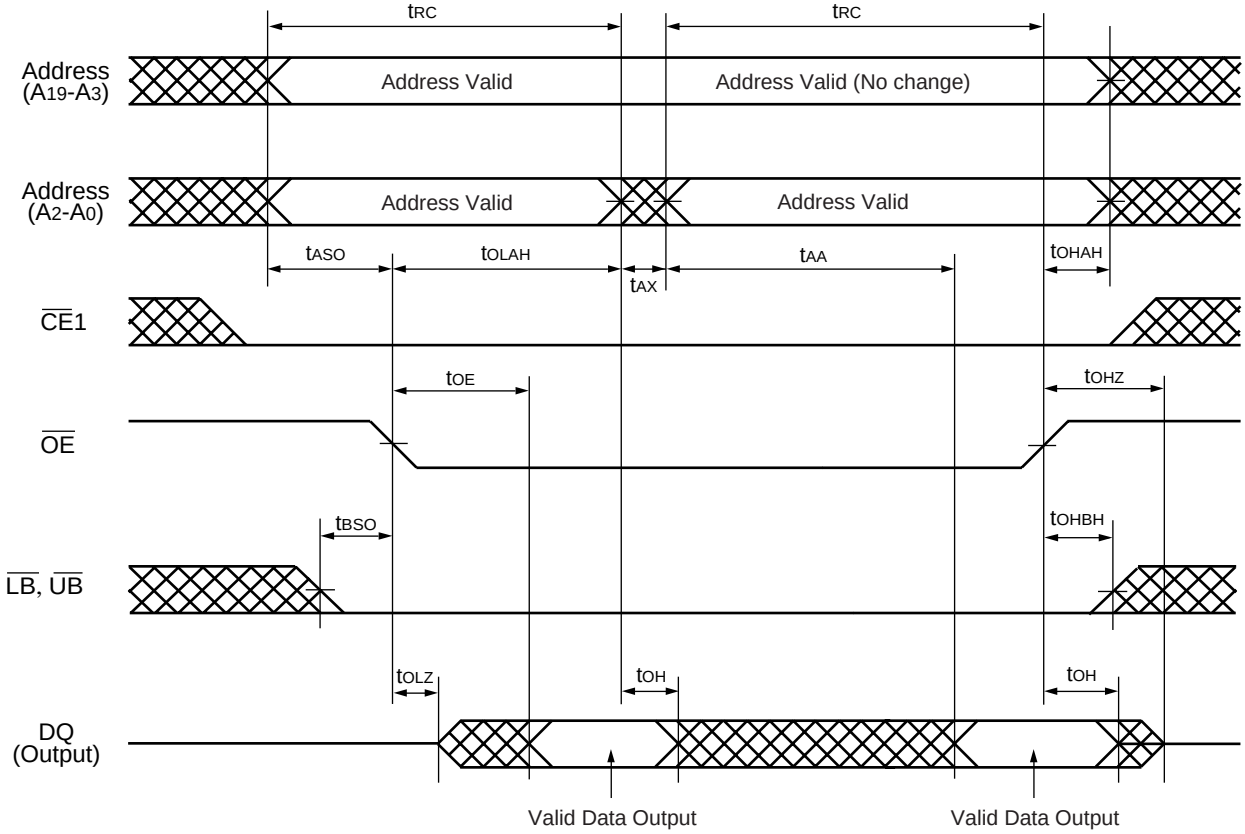
Note : CE2 and $\overline{WE}$ must be High for entire read cycle.
Either or both $\overline{LB}$ and $\overline{UB}$ must be Low when both $\overline{CE}$1 and $\overline{OE}$ are Low.

2. READ Timing #2 ($\overline{CE}$1 Control Access)



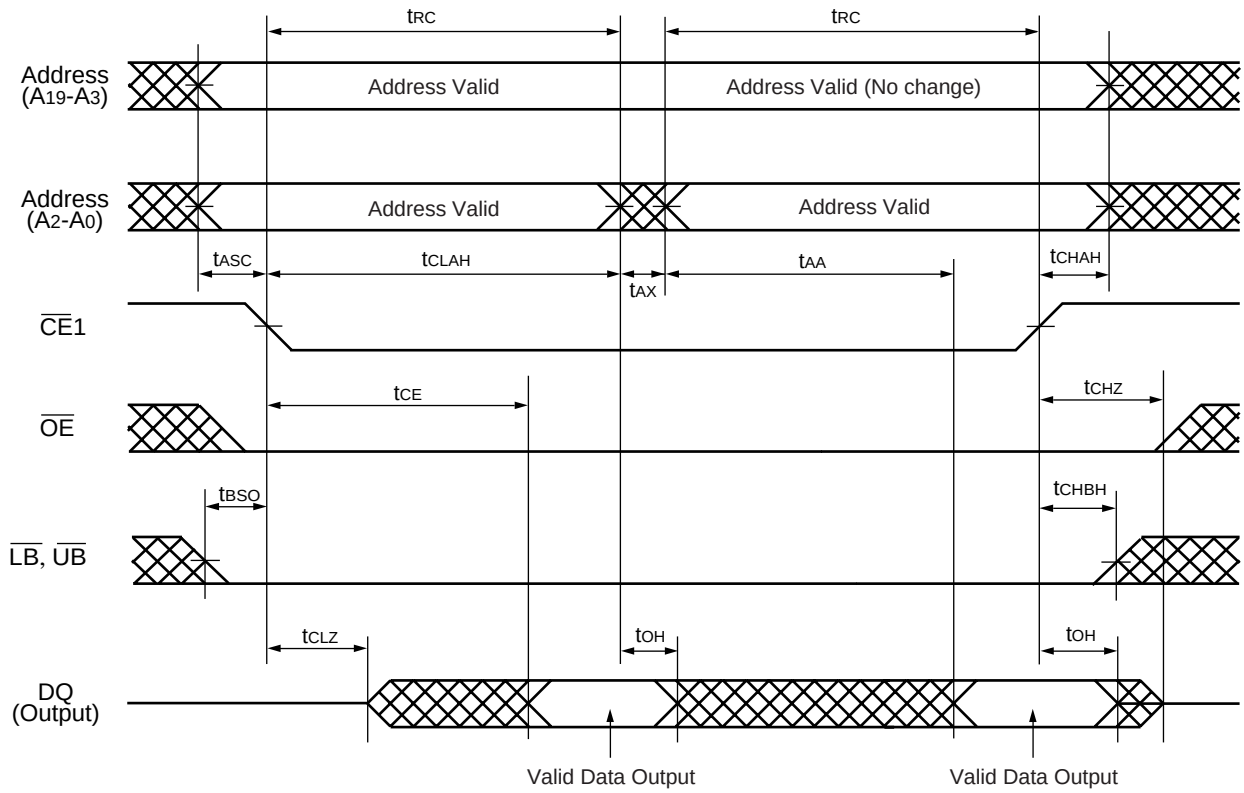
Note : CE2 and $\overline{WE}$ must be High for entire read cycle.
Either or both $\overline{LB}$ and $\overline{UB}$ must be Low when both $\overline{CE}$1 and $\overline{OE}$ are Low.

3. READ Timing #3 (Address Access after $\overline{OE}$ Control Access)



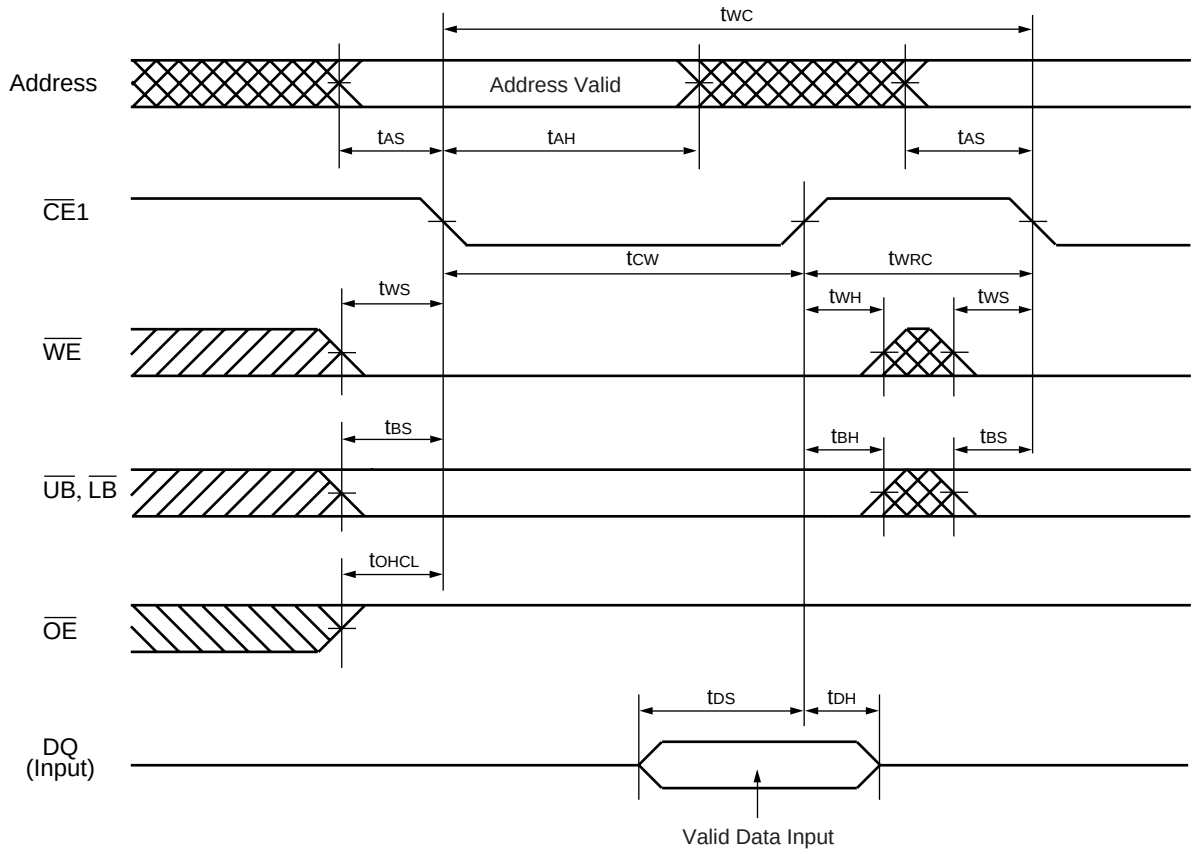
Note : CE2 and $\overline{WE}$ must be High for entire read cycle.
Either or both $\overline{LB}$ and $\overline{UB}$ must be Low when both $\overline{CE}1$ and $\overline{OE}$ are Low.

4. READ Timing #4 (Address Access after $\overline{CE}1$ Control Access)



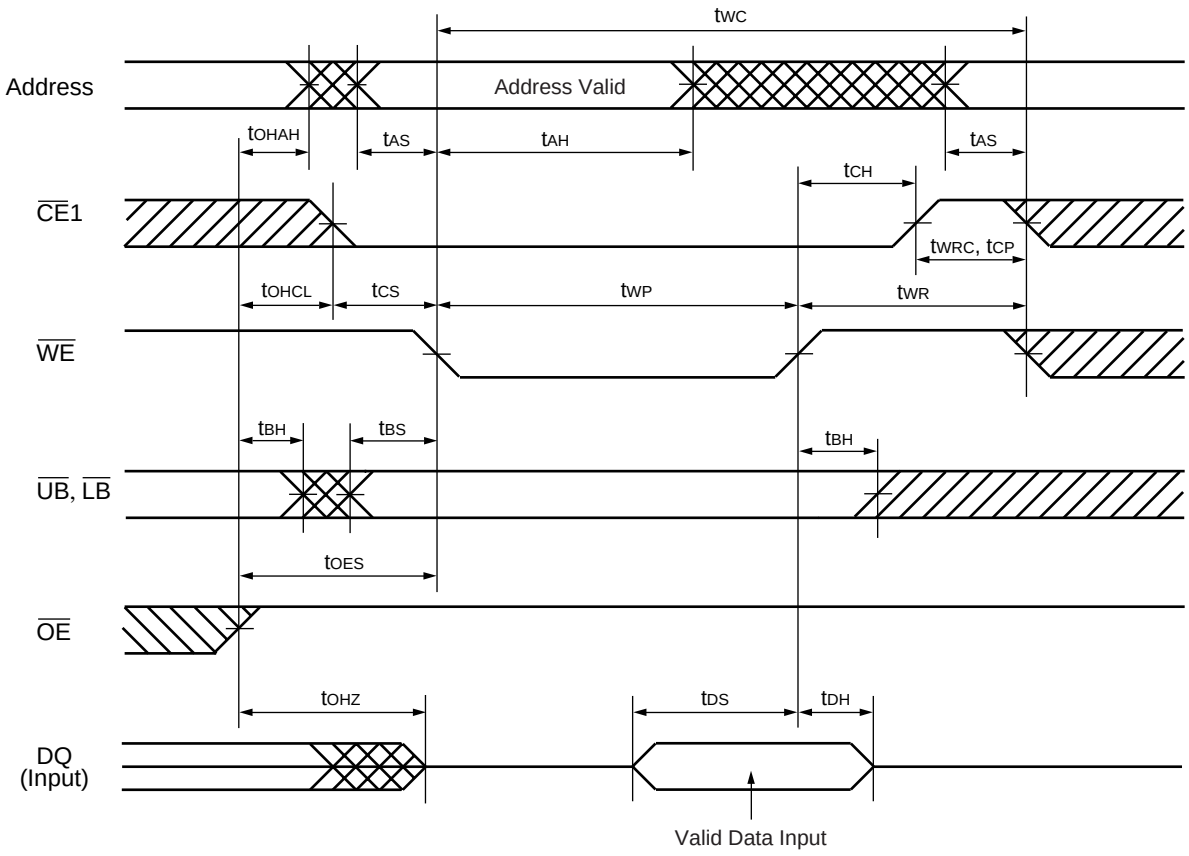
Note : CE2 and $\overline{WE}$ must be High for entire read cycle.
Either or both $\overline{LB}$ and $\overline{UB}$ must be Low when both $\overline{CE}1$ and $\overline{OE}$ are Low.

5. WRITE Timing #1 ($\overline{CE}$1 Control)



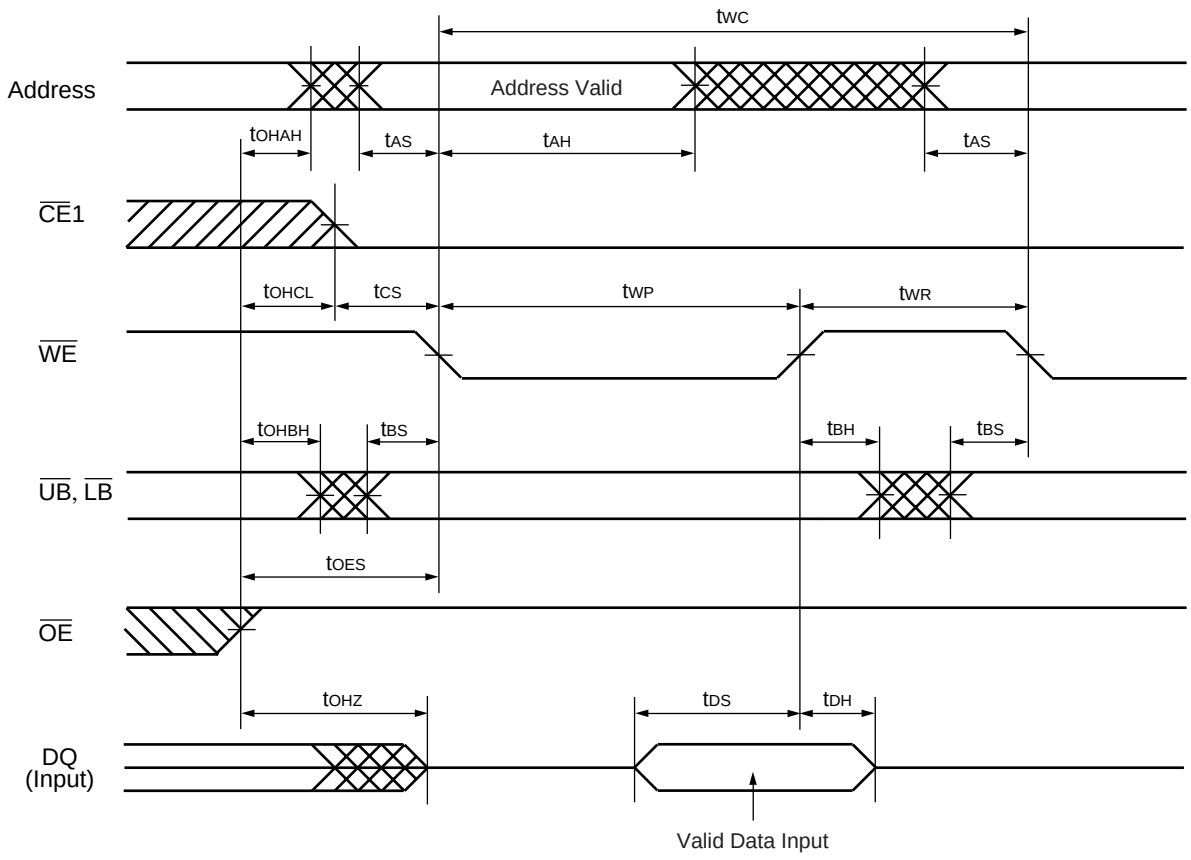
Note : CE2 must be High for write cycle.

6. WRITE Timing #2-1 ($\overline{WE}$ Control, Single Write Operation)



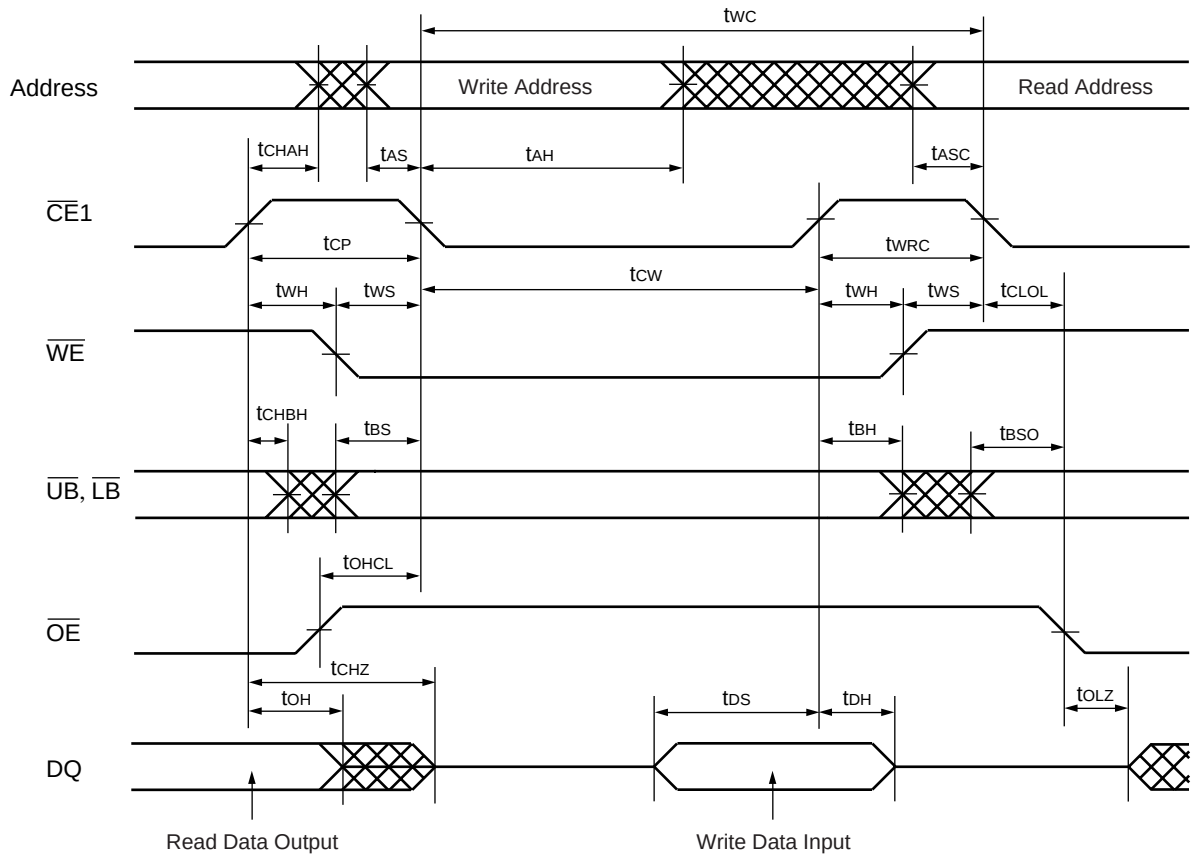
Note : CE2 must be High for write cycle.

7. WRITE Timing #2-2 ($\overline{WE}$ Control, Continuous Write Operation)



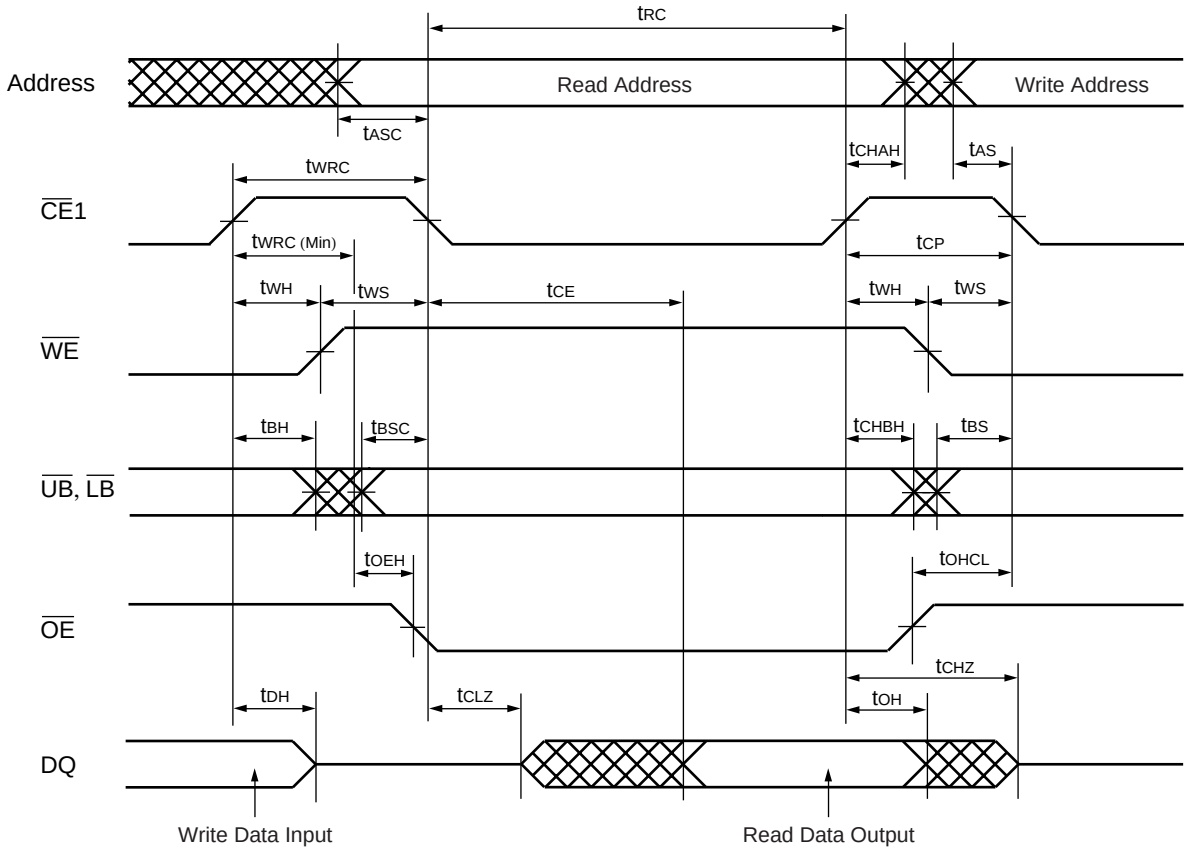
Note : CE2 must be High for write cycle.

8. READ/WRITE Timing #1-1 ($\overline{CE}$1 Control)



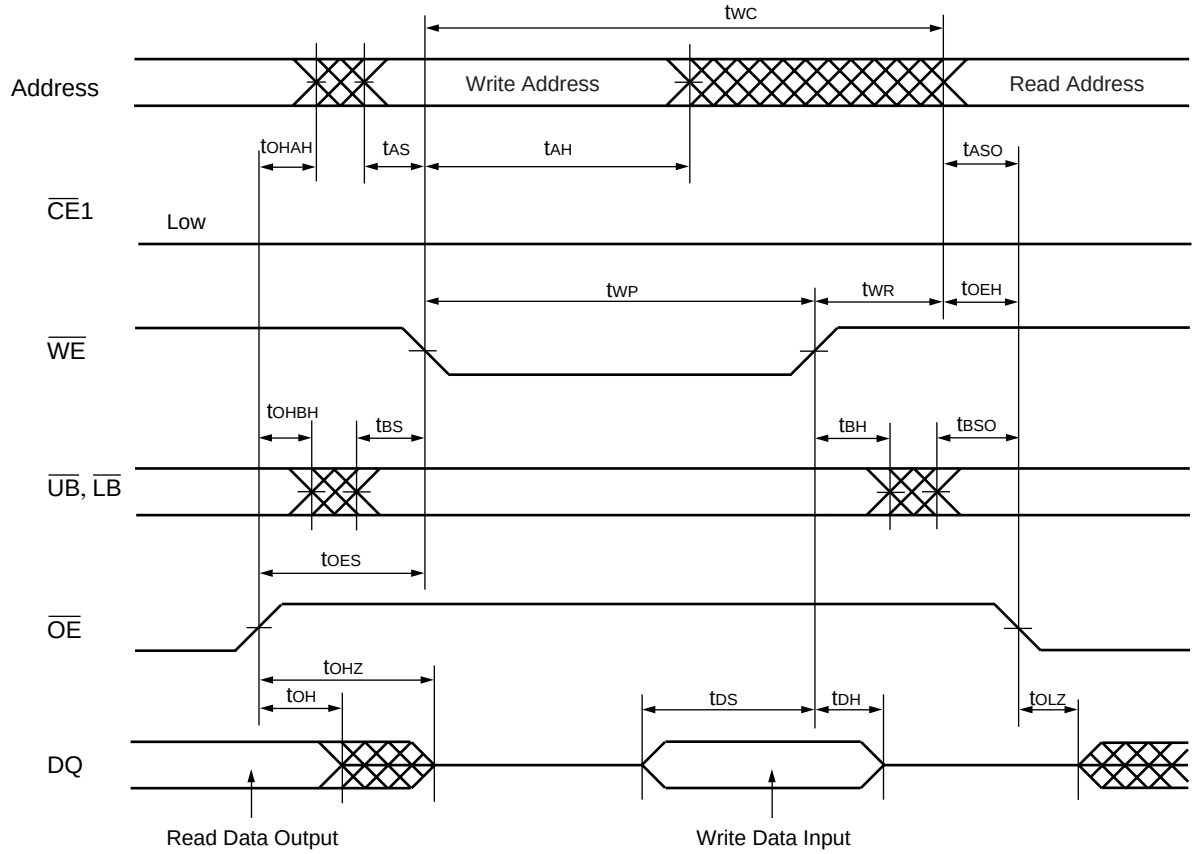
Note : Write address is valid from either $\overline{CE}$1 or $\overline{WE}$ of last falling edge.

9. READ/WRITE Timing #1-2 ($\overline{CE}$1 Control)



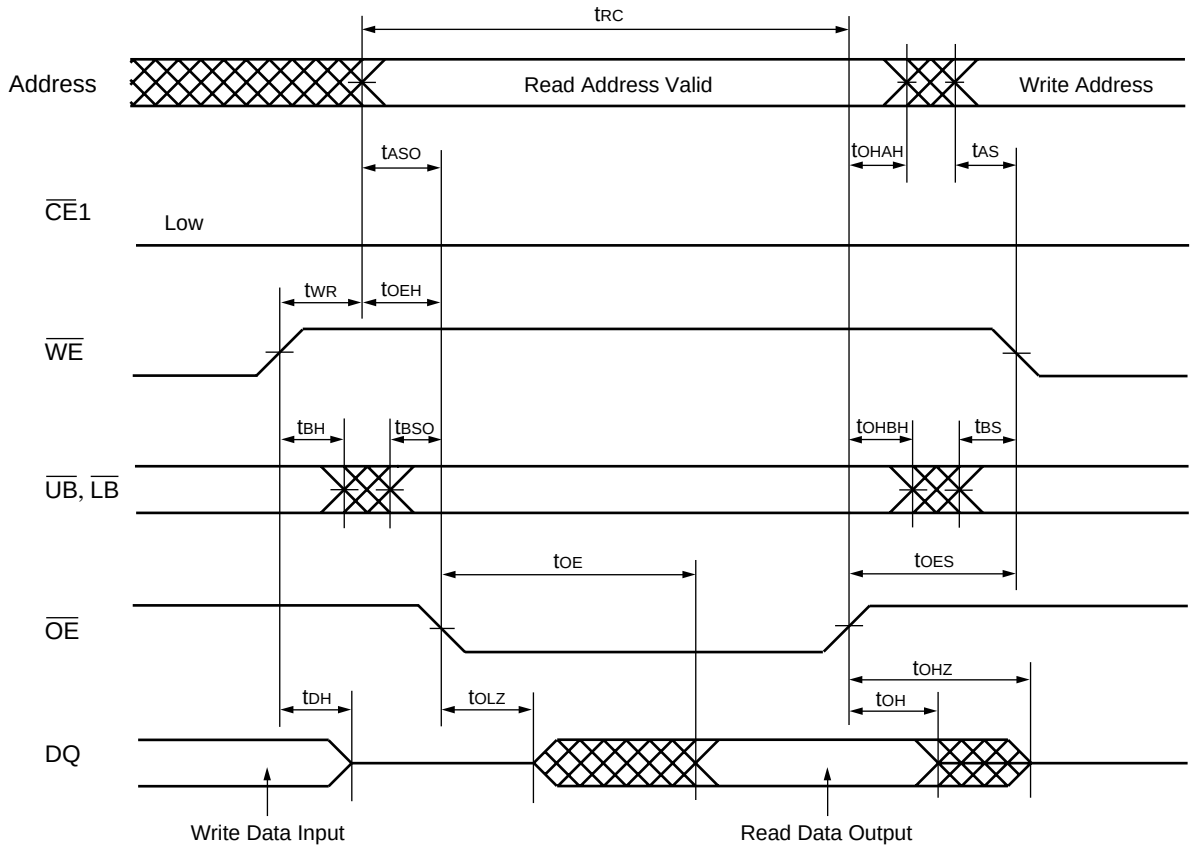
Note : The t_{OEH} is specified from the time satisfied both t_{WRC} and t_{WR} (Min) .

10. READ ($\overline{OE}$ Control) /WRITE ($\overline{WE}$ Control) Timing #2-1



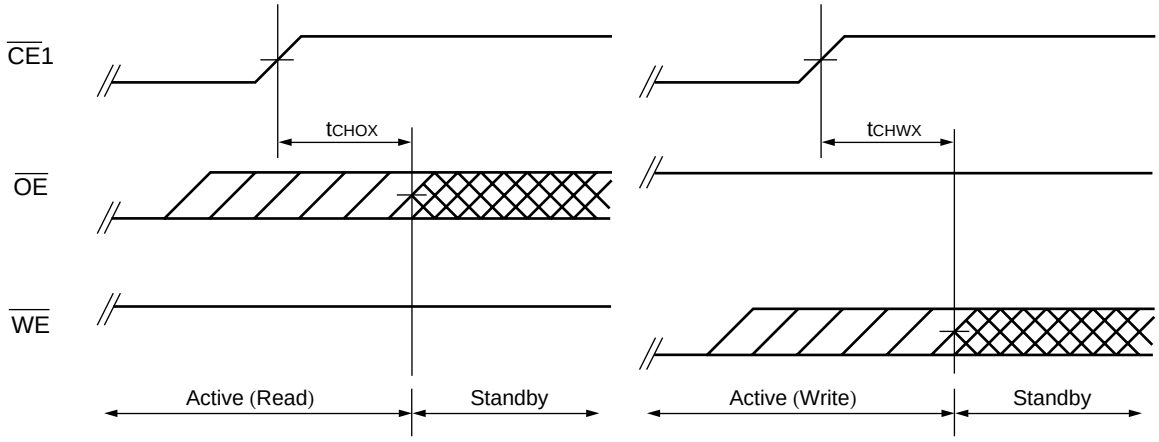
Note : $\overline{CE}1$ can be tied to Low for $\overline{WE}$ and $\overline{OE}$ controlled operation.
When $\overline{CE}1$ is tied to Low, output is exclusively controlled by $\overline{OE}$.

11. READ ($\overline{OE}$ Control) /WRITE ($\overline{WE}$ Control) Timing #2-2



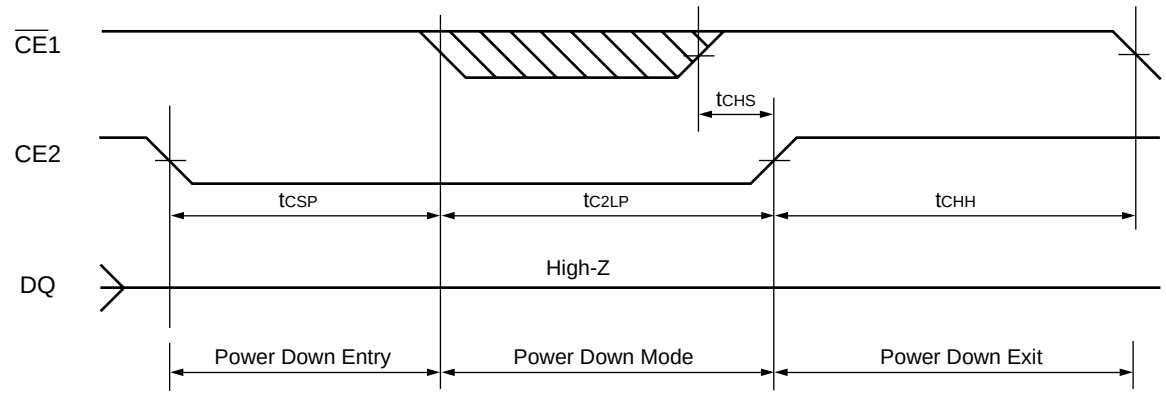
Note : $\overline{CE}$1 can be tied to Low for $\overline{WE}$ and $\overline{OE}$ controlled operation.
When $\overline{CE}$1 is tied to Low, output is exclusively controlled by $\overline{OE}$.

12. Standby Entry Timing after Read or Write



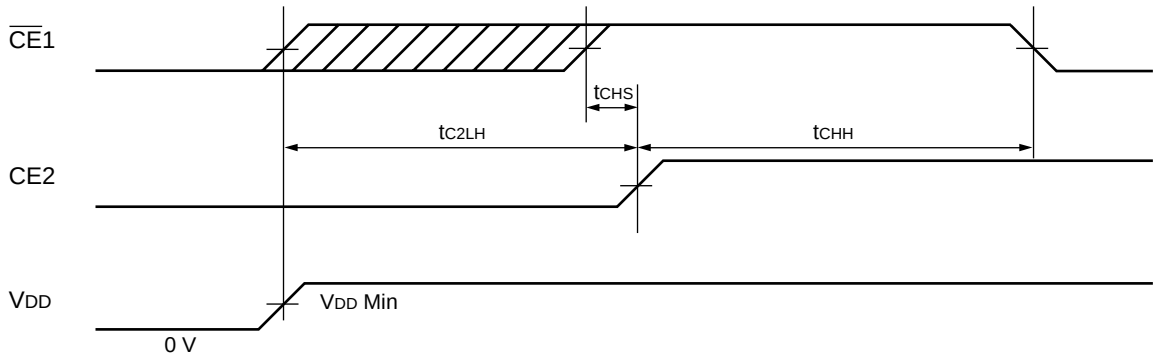
Note : Both t_{CHOX} and t_{CHWX} define the earliest entry timing for Standby mode. If either of timing is not satisfied, it takes t_{RC} (Min) period from either last address transition of A_2, A_1, and A_0, or $\overline{CE}1$ Low to High transition.

13. POWER DOWN Entry and Exit Timing



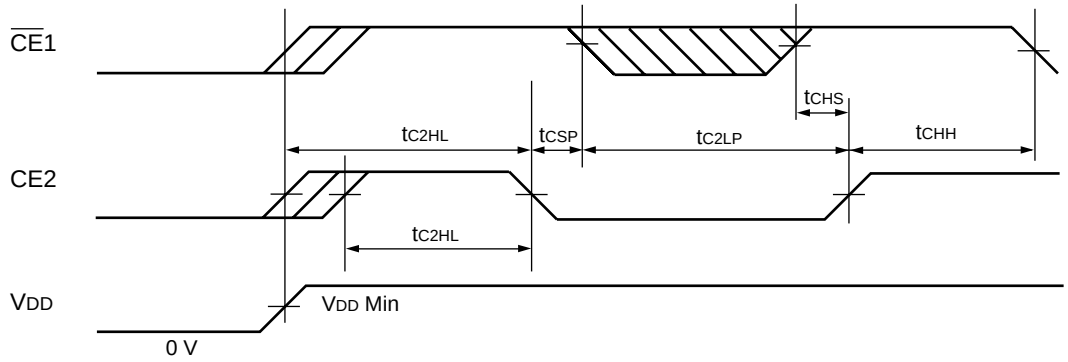
Note : This Power Down mode can be also used for Power-up #2 below.

14. POWER-UP Timing 1



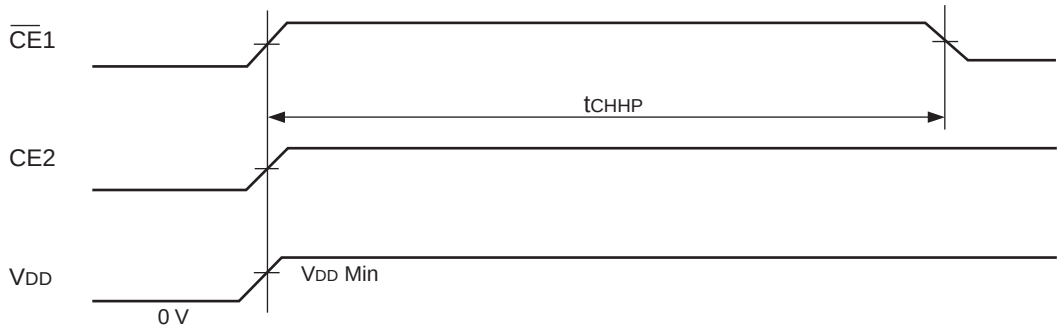
Note : The t_{C2LH} specifies after V_{DD} reaches specified minimum level.

15. POWER-UP Timing 2



Note : The t_{C2HL} specifies from CE2 Low to High transition after V_{DD} reaches specified minimum level. $\overline{CE}1$ must be brought to High prior to or together with CE2 Low to High transition.

16. POWER-UP Timing 3



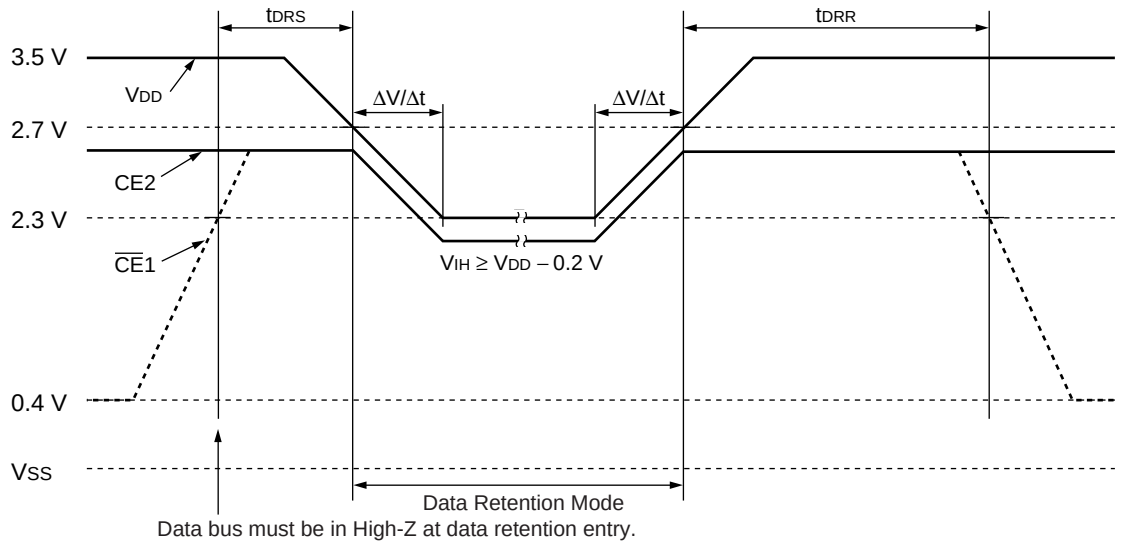
Note : Both $\overline{CE}1$ and CE2 must be High together with V_{DD}. Otherwise either POWER-UP Timing #1 or #2 must be used for proper operation.

■ DATA RETENTION

1. Low V_{DD} Characteristics

Parameter		Symbol	Test Conditions	Value		Unit
				Min	Max	
V_{DD} Data Retention Supply Voltage		V_{DR}	$\overline{CE}1 = CE2 \geq V_{DD} - 0.2$ V or $\overline{CE}1 = CE2 = V_{IH}$	2.3	3.5	V
V_{DD} Data Retention Supply Current	L Version	I_{DR1}	$V_{DD} = V_{DD}$ (23) , $V_{IN} \leq 0.2$ V or $V_{IN} \geq V_{DD} - 0.2$ V, $\overline{CE}1 = CE2 \geq V_{DD} - 0.2$ V, $I_{OUT} = 0$ mA	—	100	µA
	LL Version			—	70	
Data Retention Setup Time		t_{DRS}	$V_{DD} = V_{DD}$ at data retention entry	0	—	ns
Data Retention Recovery Time		t_{DRR}	$V_{DD} = V_{DD}$ after data retention	100	—	ns
V_{DD} Voltage Transition Time		ΔV/Δt	—	0.2	—	V/µs

2. Data Retention Timing

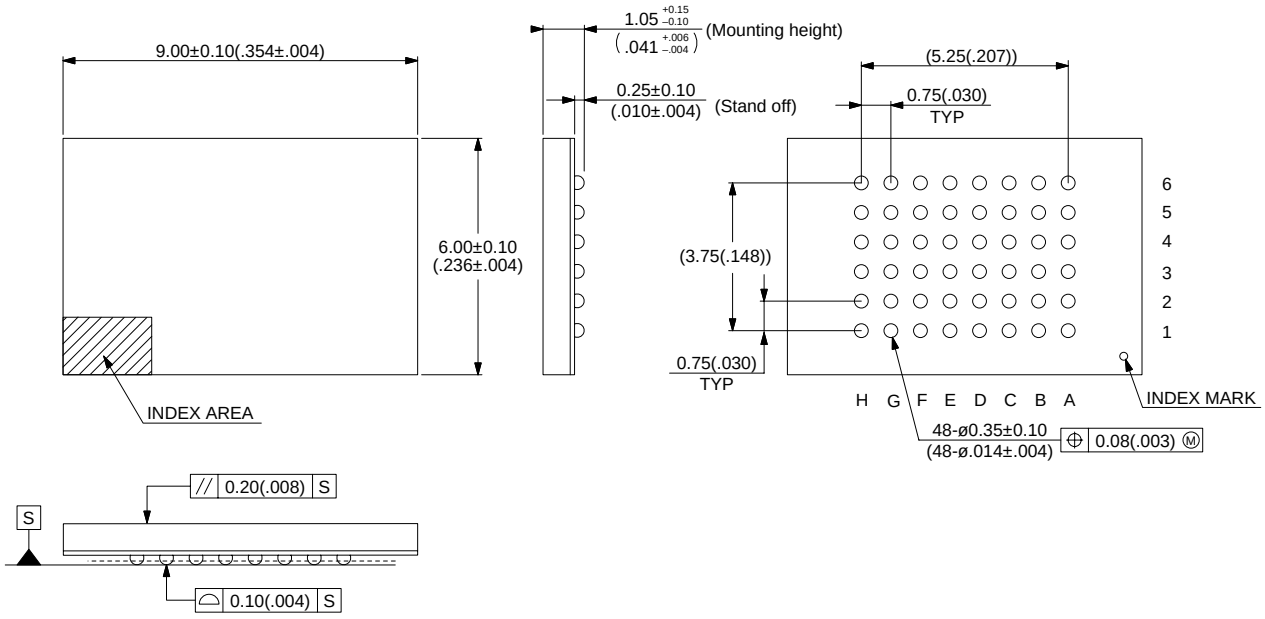


■ ORDERING INFORMATION

Part Number	Package	Remarks
MB82D01171B-60LPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	t_{CE} = 60 ns Max, I_{DDS1} = 100 µA Max
MB82D01171B-60LLPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	t_{CE} = 60 ns Max, I_{DDS1} = 70 µA Max
MB82D01171B-70LPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	t_{CE} = 70 ns Max, I_{DDS1} = 100 µA Max
MB82D01171B-70LLPBN	48-ball plastic FBGA 0.75 mm pitch (BGA-48P-M18)	t_{CE} = 70 ns Max, I_{DDS1} = 70 µA Max

■ PACKAGE DIMENSION

48-ball plastic FBGA
(BGA-48P-M18)



Dimensions in mm (inches)

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